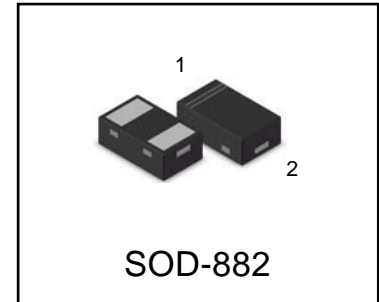


## ESD Protection Diodes with Ultra Low Capacitance

The FTV05LBUL2 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed and antenna line applications.



### Specification Features:

- Ultra Low Capacitance 3 pF
- Low Clamping Voltage
- Stand-off Voltage: 5 V
- Low Leakage
- Response Time is Typically < 1.0 ns
- IEC61000-4-2 Level 4 ESD Protection
- This is a Pb-Free Device

### Ordering information

Device	Marking	Shipping
FTV05LBUL2	Q5	10000/Tape&Reel

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±10 ±15	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	200	mW
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C
Junction Temperature Range	T <sub>J</sub>	-55 to +150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	T <sub>L</sub>	260	°C

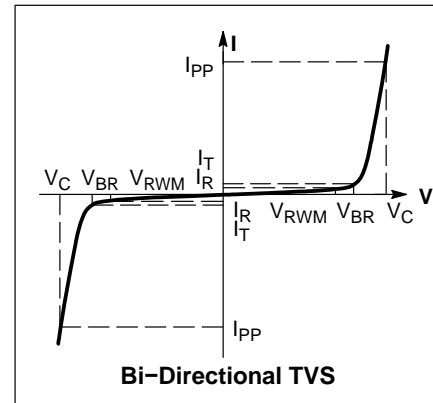
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0 x 0.75 x 0.62 in.

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

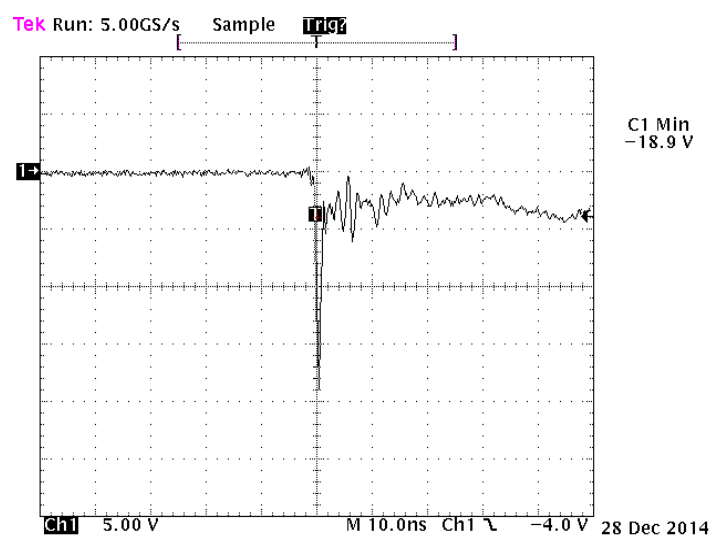
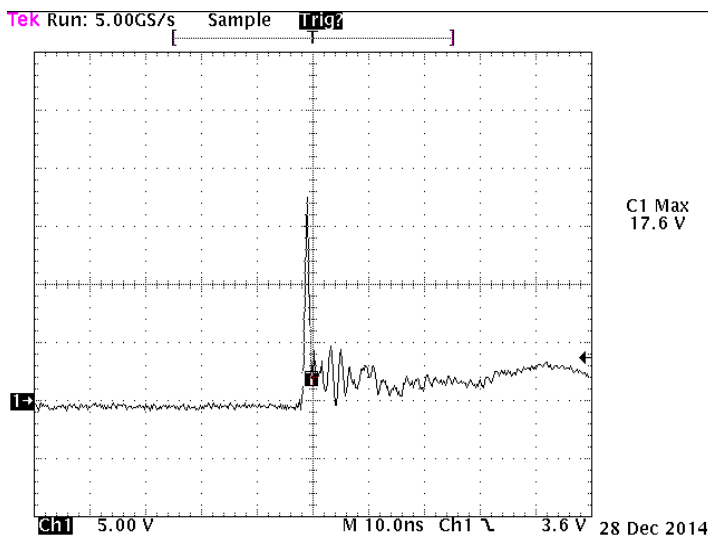
Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$P_{pk}$	Peak Power Dissipation
C	Capacitance @ $V_R = 0$ and $f = 1.0$ MHz



## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Device	Device Marking	$V_{RWM}$ (V)	$I_R$ ( $\mu\text{A}$ ) @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T = 1\text{mA}$ (Note 2)	C (pF)		$V_C$ (V) @ $I_{PP} = 2.5\text{A}$ (Note 3)	$I_{PP}$ (A) $t_p=8/20\mu\text{s}$	$P_{PP}$ (W)	$V_C$
		Max	Max	Min	Typ	Max	Max	Max	Max	Per IEC61000-4-2 (Note4)
FTV05LBUL2	Q 5	5.0	0.5	6.0	2.5	3	12.1	2.5	30	Figures 1 and 2 See Below

- $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$ .
- Surge current waveform per Figure 4.
- For test procedure see Figures 3.



IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

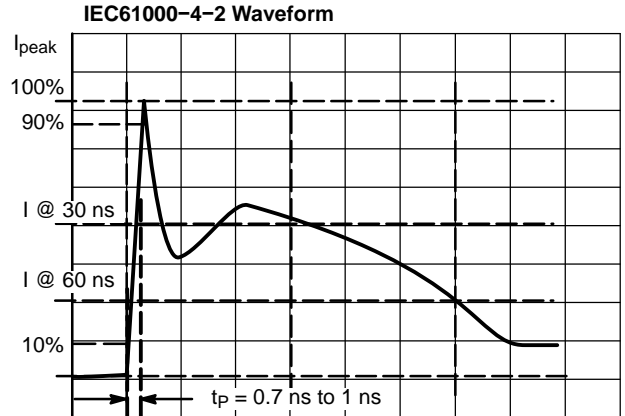


Figure 3. IEC61000-4-2 Spec

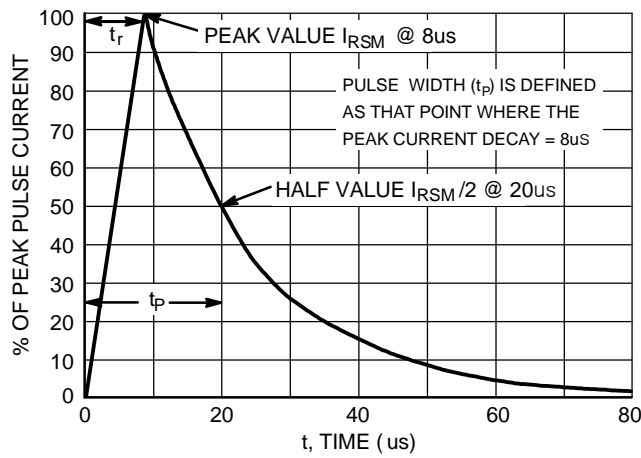


Figure 4. 8 X 20 us Pulse Waveform

## SOD-882

DIMENSION OUTLINE:

Unit:mm

